



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03A Plastic-Encapsulate Transistors

THA92TTD03 TRANSISTOR

DESCRIPTION

PNP Epitaxial Silicon Transistor

FEATURES

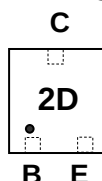
Power dissipation P_{CM} : 0.15 W ($T_{amb}=25^{\circ}C$)

APPLICATION

High Voltage Amplifier

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING:2D

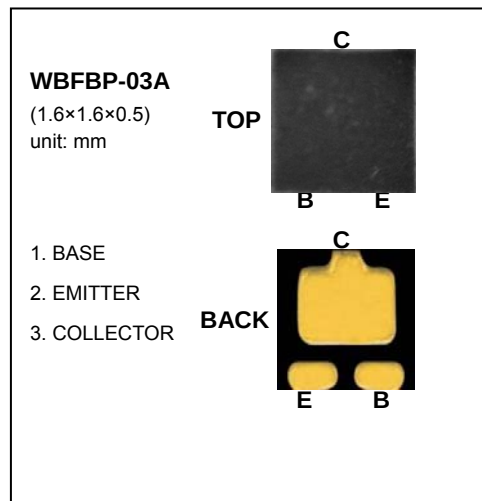


MAXIMUM RATINGS $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-310	V
V_{CEO}	Collector-Emitter Voltage	-305	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-300	mA
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-310		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-305		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -200V, I_E = 0$		-0.25	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -200V, I_B = 0$		-0.25	μA
		$V_{CE} = -300V, I_B = 0$		-5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -1mA$	60		
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -10mA$	100	200	
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -30mA$	60		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$		-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$		-0.9	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA$ $f = 30MHz$	50		MHz



Typical Characteristics

THA92TTD03

